

# 2N6426, 2N6427

2N6426 is a Preferred Device

## Darlington Transistors

### NPN Silicon

#### Features

- These are Pb-Free Devices\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	40	Vdc
Collector – Base Voltage	$V_{CB0}$	40	Vdc
Emitter – Base Voltage	$V_{EBO}$	12	Vdc
Collector Current – Continuous	$I_C$	500	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

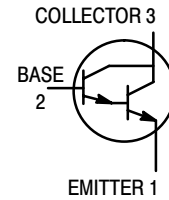
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

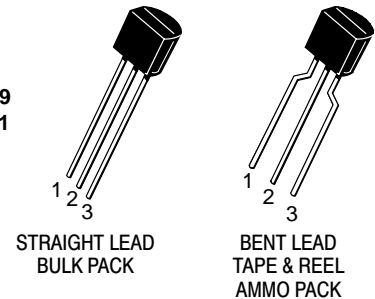


ON Semiconductor®

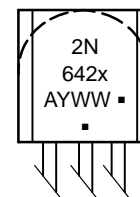
<http://onsemi.com>



TO-92  
CASE 29  
STYLE 1



#### MARKING DIAGRAM



- x = 6 or 7
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 2N6426, 2N6427

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage, (Note 1) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>BE</sub> = 0)	V <sub>(BR)CEO</sub>	40	–	–	V <sub>dc</sub>
Collector–Base Breakdown Voltage (I <sub>C</sub> = 100 μA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	40	–	–	V <sub>dc</sub>
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 10 μA <sub>dc</sub> , I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	12	–	–	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = 25 V <sub>dc</sub> , I <sub>B</sub> = 0)	I <sub>CES</sub>	–	–	1.0	μA <sub>dc</sub>
Collector Cutoff Current (V <sub>CB</sub> = 30 V <sub>dc</sub> , I <sub>E</sub> = 0)	I <sub>CBO</sub>	–	–	50	nA <sub>dc</sub>
Emitter Cutoff Current (V <sub>EB</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	–	50	nA <sub>dc</sub>
<b>ON CHARACTERISTICS</b>					
DC Current Gain, (Note 1) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )	h <sub>FE</sub>	20,000 10,000	– –	200,000 100,000	–
(I <sub>C</sub> = 100 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )		30,000 20,000	– –	300,000 200,000	
(I <sub>C</sub> = 500 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )		20,000 14,000	– –	200,000 140,000	
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 50 mA <sub>dc</sub> , I <sub>B</sub> = 0.5 mA <sub>dc</sub> ) (I <sub>C</sub> = 500 mA <sub>dc</sub> , I <sub>B</sub> = 0.5 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	– –	0.71 0.9	1.2 1.5	V <sub>dc</sub>
Base–Emitter Saturation Voltage (I <sub>C</sub> = 500 mA <sub>dc</sub> , I <sub>B</sub> = 0.5 mA <sub>dc</sub> )	V <sub>BE(sat)</sub>	–	1.52	2.0	V <sub>dc</sub>
Base–Emitter On Voltage (I <sub>C</sub> = 50 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )	V <sub>BE(on)</sub>	–	1.24	1.75	V <sub>dc</sub>
<b>SMALL–SIGNAL CHARACTERISTICS</b>					
Output Capacitance (V <sub>CB</sub> = 10 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	–	5.4	7.0	pF
Input Capacitance (V <sub>EB</sub> = 1.0 V <sub>dc</sub> , I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	–	10	15	pF
Input Impedance (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>ie</sub>	100 50	– –	2000 1000	kΩ
Small–Signal Current Gain (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>fe</sub>	20,000 10,000	– –	– –	–
Current–Gain – High Frequency (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> , f = 100 MHz)	h <sub>fe</sub>	1.5 1.3	2.4 2.4	– –	–
Output Admittance (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>oe</sub>	–	–	1000	μmhos
Noise Figure (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> , R <sub>S</sub> = 100 kΩ, f = 1.0 kHz)	NF	–	3.0	10	dB

1. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

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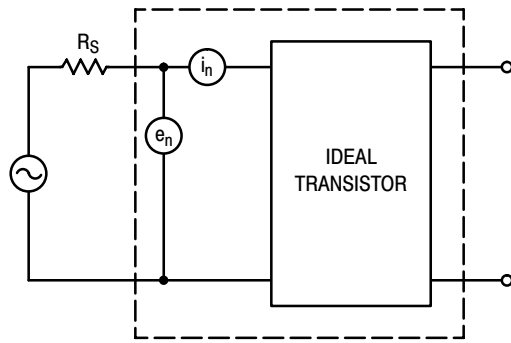


Figure 1. Transistor Noise Model

### NOISE CHARACTERISTICS

( $V_{CE} = 5.0 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ )

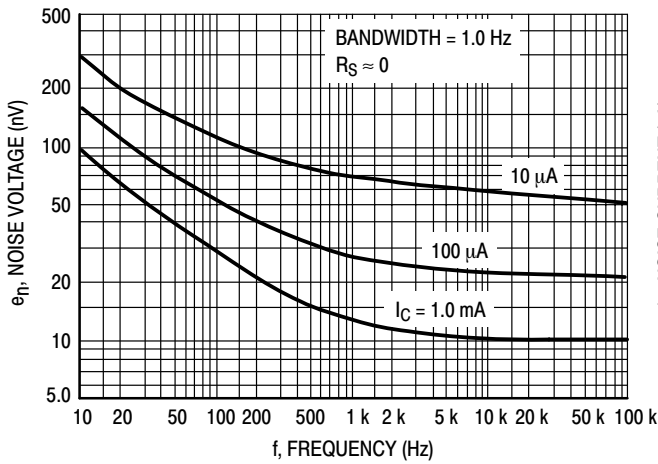


Figure 2. Noise Voltage

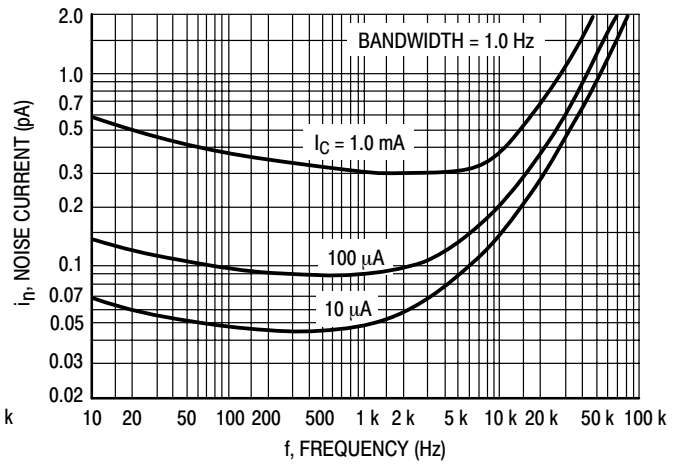


Figure 3. Noise Current

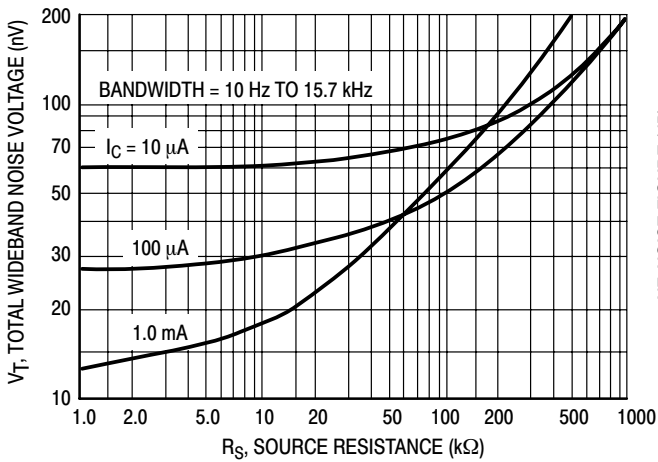


Figure 4. Total Wideband Noise Voltage

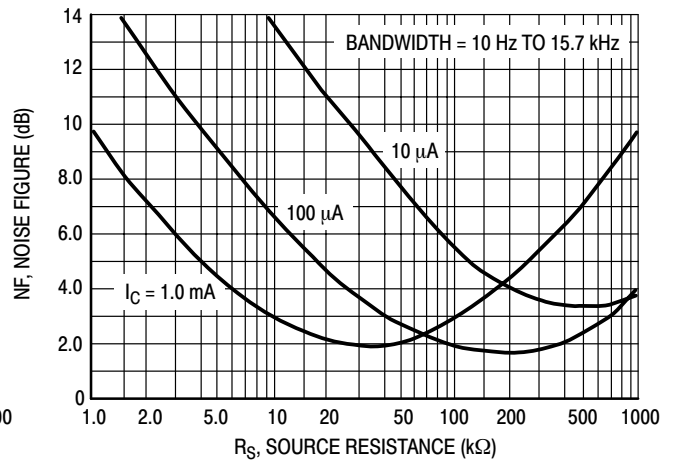


Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

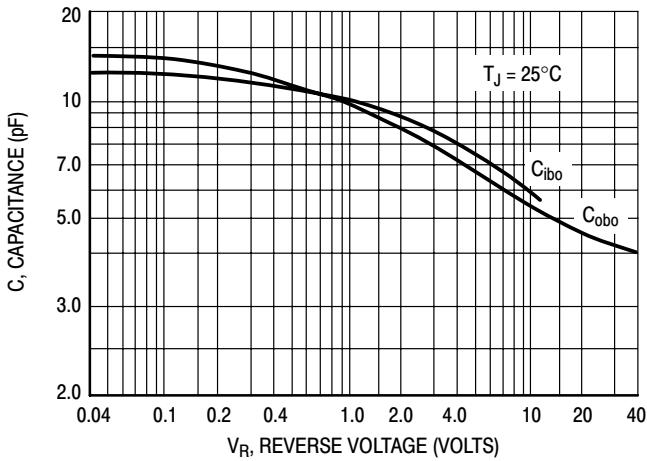


Figure 6. Capacitance

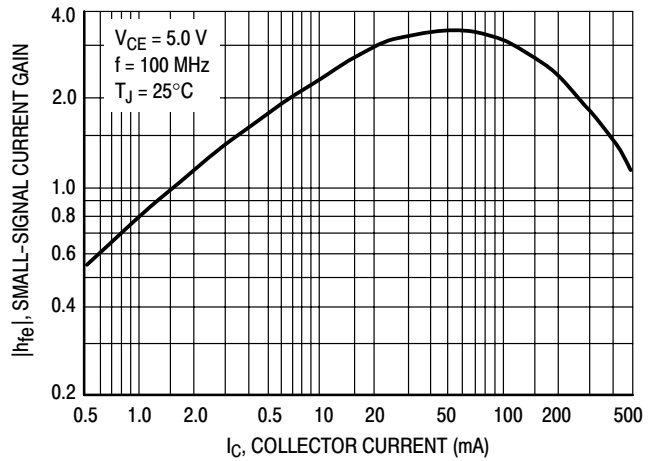


Figure 7. High Frequency Current Gain

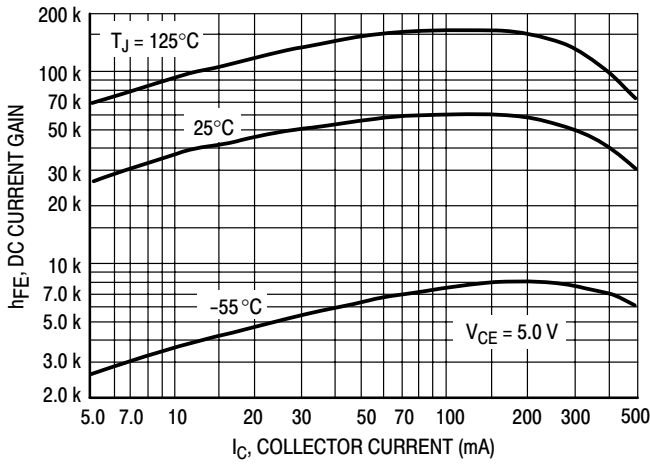


Figure 8. DC Current Gain

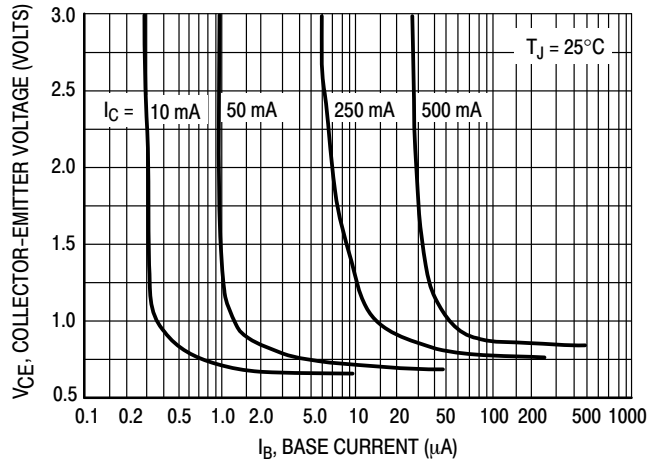


Figure 9. Collector Saturation Region

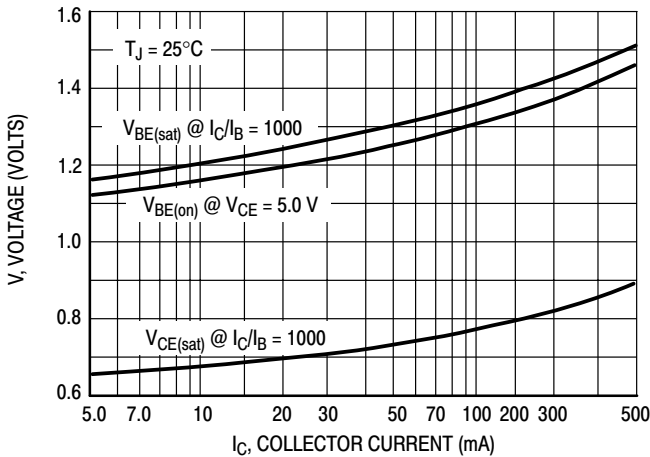


Figure 10. "On" Voltages

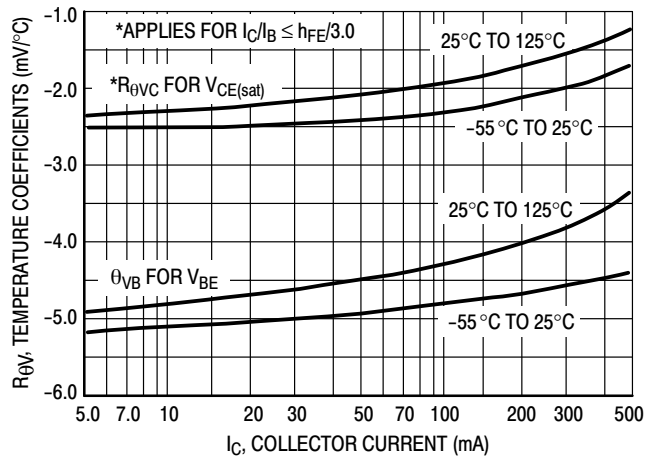
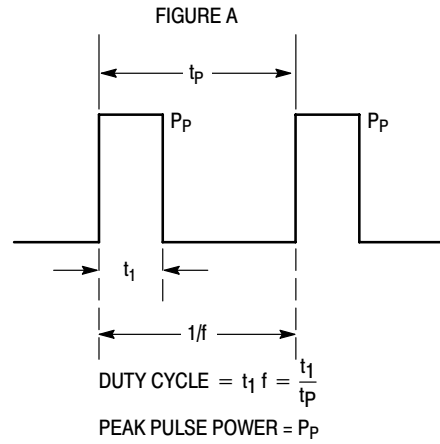
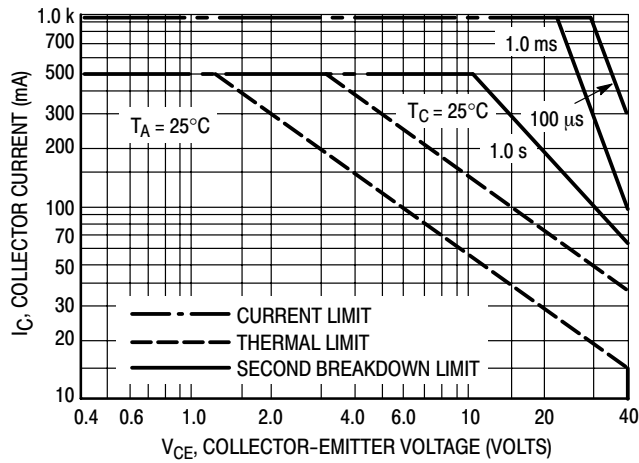
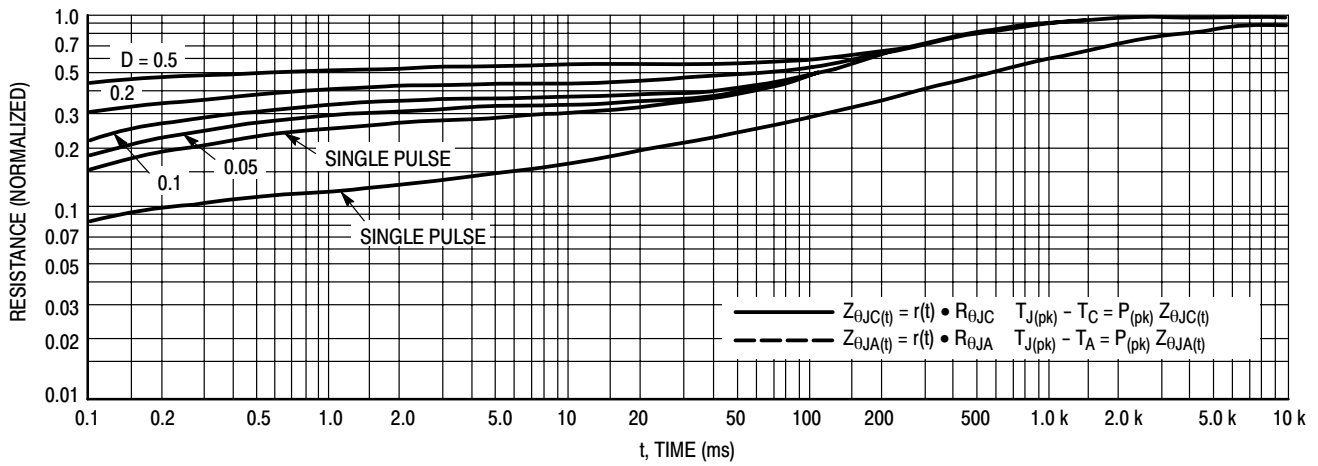


Figure 11. Temperature Coefficients

## 2N6426, 2N6427



**Design Note: Use of Transient Thermal Resistance Data**

### ORDERING INFORMATION

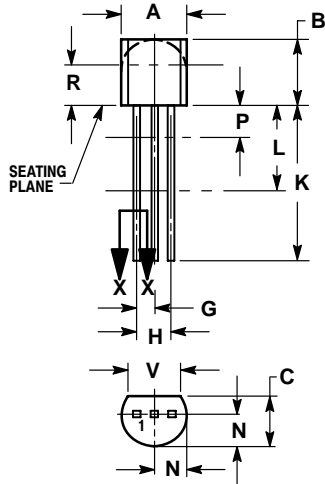
Device	Package	Shipping†
2N6426G	TO-92 (Pb-Free)	5,000 Units / Bulk
2N6426RLRAG	TO-92 (Pb-Free)	2,000 / Tape & Ammo
2N6427G	TO-92 (Pb-Free)	5,000 Units / Bulk
2N6427RLRAG	TO-92 (Pb-Free)	2,000 / Tape & Ammo

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

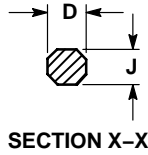
# 2N6426, 2N6427

## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-11  
ISSUE AM



STRAIGHT LEAD  
BULK PACK

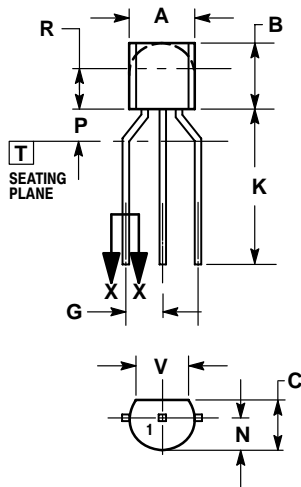


SECTION X-X

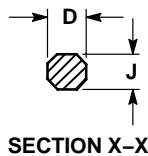
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD  
TAPE & REEL  
AMMO PACK



SECTION X-X


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 1:

1. PIN 1. EMITTER
2. BASE
3. COLLECTOR

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